

Fei Tong

List of Publications by Year in descending order

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Version: 2024-02-01

13
papers

162
citations

1307594

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1125743

13
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14
all docs

14
docs citations

14
times ranked

357
citing authors

#	ARTICLE	IF	CITATIONS
1	Negative field-dependent charge mobility in crystalline organic semiconductors with delocalized transport. <i>Chemical Papers</i> , 2018, 72, 1685-1695.	2.2	5
2	Role of transport band edge variation on delocalized charge transport in high-mobility crystalline organic semiconductors. <i>Physical Review B</i> , 2017, 96, .	3.2	8
3	Simulation of the Refractive Index of Ga Doped ZnO Nanoparticles Embedded in PEDOT:PSS Using Effective Medium Approximations. <i>Journal of Nanoscience and Nanotechnology</i> , 2016, 16, 7358-7362.	0.9	2
4	Solution-Based Fabrication of Carbon Nanotube Bumps for Flip-Chip Interconnects. <i>IEEE Nanotechnology Magazine</i> , 2014, 13, 1118-1126.	2.0	6
5	Surface plasmon resonance properties of DC magnetron sputtered Ag nanoislands on ITO-glass and In ₂ O ₃ -PET substrates. <i>Electronics Letters</i> , 2014, 50, 623-624.	1.0	1
6	Depth-resolved ultra-violet spectroscopic photo current-voltage measurements for the analysis of AlGaIn/GaN high electron mobility transistor epilayer deposited on Si. <i>Applied Physics Letters</i> , 2014, 105, 172105.	3.3	7
7	Growth of nanostructured ZnO on wearable fabrics for functional garment. <i>Materials Letters</i> , 2014, 118, 47-50.	2.6	9
8	Spectroscopic photo ν diagnostics of nitride-based high electron mobility transistor structures on Si wafers. <i>Electronics Letters</i> , 2013, 49, 1547-1548.	1.0	7
9	Biofunctionalized AlGaIn/GaN high electron mobility transistor for DNA hybridization detection. <i>Applied Physics Letters</i> , 2012, 100, .	3.3	36
10	Flexible organic/inorganic hybrid solar cells based on conjugated polymer and ZnO nanorod array. <i>Semiconductor Science and Technology</i> , 2012, 27, 105005.	2.0	20
11	Growth of ZnO Nanorod Arrays on Flexible Substrates: Effect of Precursor Solution Concentration. <i>ISRN Nanomaterials</i> , 2012, 2012, 1-7.	0.7	13
12	Electrical characteristics of the vertical GaN rectifiers fabricated on bulk GaN wafer. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011, 8, 2430-2432.	0.8	12
13	Ultra-low leakage and high breakdown Schottky diodes fabricated on free-standing GaN substrate. <i>Semiconductor Science and Technology</i> , 2011, 26, 022002.	2.0	36